L	Hits	Search Text		
Number			DB ·	Time stamp
1	1974		USPAT;	2004/05/18
	1	(nucleat\$ seed\$))	US-PGPUB	16:06
2	399	1 ( ( \	USPAT;	2004/05/18
•		(nucleat\$ seed\$))) and (implants)	US-PGPUB	16:04
3	288	((((nitride "si.sub.3 n.sub.4") with	USPAT;	
		(nucleat\$ seed\$))) and (implant\$)) not		. 2004/05/18
		(@ad>20010723 or @rlad>20010723)	US-PGPUB	16:07
4 ·	204	(///pitride Wei 23)		
	. 201	1 ( ( ( ( ( ( ( ( ( ( ( ( ( ( ( ( ( ( (	USPAT;	2004/05/18
		(nucleat\$ seed\$))) and (implant\$)) not	US-PGPUB	16:07
		(@ad>20010723 or @rlad>20010723)) and		
-		nucleat\$		0.00
5 4 4	160757		USPAT;	2004/05/18
•		(nucleat\$ seed\$)) same2 implant\$	US-PGPUB	
6	62	((nitride "si.sub.3 n.sub.4") with	02-FGFÓB	16:07
	į	(nucleat\$ seed\$)) same implant\$	USPAT;	2004/05/18
7	45	(//nitride "mi and 2	US-PGPUB	18:35
	13	1 ( ( ( )	USPAT;	2004/05/18
	,	(nucleat\$ seed\$)) same implant\$) not	US-PGPUB	16:07
0	1.	(@ad>20010723 or @rlad>20010723)		
8 .	. 34	((((nitride "si.sub.3 n.sub.4") with	USPAT;	2004 (05 (10)
	1	(nucleat\$ seed\$)) same implant\$) not		2004/05/18
		(Gad>20010723 or Grlad>20010723)) and	US-PGPUB	16:17
	1	nucleats		
9	11		1	
••			- USPAT;	2004/05/18
		(nucleat\$ seed\$)) same implant\$) not	US-PGPUB	16:17
	9)(0	(@ad>20010723 or @rlad>20010723)) not		
		(((((nitride "si.sub.3 n.sub.4") with	· .	
		(nucleat\$ seed\$)) same implant\$) not	-	
	:	(@ad>20010723 or @rlad>20010723)) and	`	
		nucleat\$ )		- 1
10 .	243	Mucleacy	`	
	443		USPAT;	2004/05/18
-ā	-0	(nucleat\$ seed\$))) and (implant\$)) not	US-PGPUB	16:20
	٠.	(@ad>20010723 or @rlad>20010723)) not	1 10100	1 +0.20
		(((nitride "si.sub.3 n sub.4") with	1	1
		(nucleat\$ seed\$)) same implant\$)	* * * * 1	
11	165'902	438/\$.ccls. or 257/\$.ccls.	*	
		237/3.CCIS.	USPAT;	2004/05/18
12.	197	111111	US-PGPUB	16:21
	. 197	((((((nitride "si.sub.3 n.sub.4") with	USPAT;	2004/05/18
1		(nucleat\$ seed\$))) and (implant\$)) not	US-PGPUB	19:09
-		(@ad>20010723 or @rlad>20010723)) not	1 01 0D	19.09
		(((nitride "si.sub.3 n.sub.4") with		100
		(nucleat\$ seed\$)) same implant\$)) and		
		(438/\$.ccls. or 257/\$.ccls.)		
L3 ·	.42	(angles noon implement	1.	1
	- 74	(angle\$ near implant\$) and (nitride with	USPAT;	2004/05/18
4	1	uniforms) /	US-PGPUB	18:25
.4	156	'(implant\$) same (nitride with uniform\$)	USPAT;	2004/05/18
			US-PGPUB	
.5	. 2	<pre>(implant\$) same (nitride with uniform\$)</pre>		18:27
		same (nucleat\$)	USPAT;	2004/05/18
6	131	((implants) same (nithing	US-PGPUB	18:26
		((implants) same (nitride with uniforms))	USPAT;	2004/05/18
7	7	and (438/\$.ccls. or 257/\$.ccls.)	US-PGPUB	18:26
·	,-	(implant\$) same (nitride with uniform\$)	USPAT;	2004/05/18
	. 1	same angle\$	US-PGPUB	
8	5	(ion adj implant) with (nucleat\$)	IICDAM.	18:27
. 1		· · · · · · · · · · · · · · · · · · ·	USPAT;	2004/05/18
. 1	119259	438/\$.ccls. or 257/\$.ccls.	US-PGPUB	19:09
[-	1	201/9.CCIS.	USPAT;	2003/02/13
ı	12479	/implanting and	US-PGPUB	15:43
	+4.717	(implanting implanted implant) with	USPAT;	2003/02/14
		(nitrogen trifluoronitride ammonia	US-PGPUB	10:59
		i just allulonia		TO:09
		(nitrous adi oxide) (nitric adi ovido)	05 10100	
		(nitrous adi oxide) (nitric adi ovido)	0 P 1 G 1 G B	*
		(nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh sub 3" "n sub 2	05 /1010B	*
		(nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")		*
	13765	(nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no") (implanting implanted implant) with	USPAT;	2003/02/13
	13765	(nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no") (implanting implanted implant) with (silicon (silicon adj tetrafluoride)	USPAT;	2003/02/13
	13765	(nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no") (implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilando		2003/02/13 15:47
	13765	(nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no") (implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF sub 4"	USPAT;	
	13765	(nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no") (implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub 2 cl sub 2"	USPAT;	
	13765	(nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no") (implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilando	USPAT;	

-		<u> </u>		
	47	94 (438/\$.ccls. or 257/\$.ccls.) and	USPAT;	1 2002 (00 /14
	3	((implanting implanted implant) with	1 ' '	2003/02/14
1		(nitrogen trifluoronitride ammonia	US-PGPUB	10:53
		(mittogen triffuoronitride ammonia		
	·  .	(nitrous adj oxide) (nitric adj oxide)		
	· .	"n.sub.2" "nf.sub.3" "nh sub 3" "n sub 2		·
. "	1	o" "no"))		
	119	2 //39/6 ==1= == 057/4		
9	.   ***		USPAT;	2003/02/13
	- 1	((implanting implanted implant) with	US-PGPUB	15:47
	Y Y	(silicon (silicon adj tetrafluoride)	05.10105	13.47
· 4.		silane dichlorosilane trichlorosilande	•	
		strane dichiorosilane trichiorosilande		
		(silicon adj tetrachloride) "siF.sub.4"		*
	İ	"siH.sub4" "siH.sub.2 cl.sub.2"		
		"siCl.sub.3" "sicl.sub.4"))		
		4 ((438/\$ ccls or 257/\$ ccls ) and	,	
		-   \  \	USPAT;	2003/02/13
		((implanting implanted implant) with	US-PGPUB	15:54
		(silicon (silicon adj tetrafluoride)	OB TOPOB	13.54
		silane dichlorosilane trichlorosilande	,	-
	1 . "	sitalle dichiorosilane trichiorosilande	,	
	4	(silicon adj tetrachloride) "siF.sub.4"		T .
		"SiH.sub4" "siH.sub.2 cl.sub 2"		*
		"siCl.sub.3" "sicl.sub.4"))) and (uniform		
, ***	1	noons thickness sub.4 ))) and (uniform		
		near3 thickness\$ near3 dielectric)	9 av	1
- ,	] ]	2 ((438/\$.ccls. or 257/\$.ccls.) and	USPAT;	2003/02/13
·		((implanting implanted implant) with		
		(nitrogen trifluoronitride ammonia	US-PGPUB	16:04
		(mit-royen clilluoronitride ammonia	1	4
	والساء والمراكرات	(nitrous adj oxide) (nitric adj oxide)		
	1	"n. sub. 2" "nf. sub. 3" "nh. sub. 3" "n sub. 2		
	-	o" "no"))) and (uniform near3 thickness\$		· ·
		noon? dial-ata (dilitotim hears thicknesss		
1	1	near3 dielectric)		
•	) 3	(((438/\$.ccls. or 257/\$.ccls.) and	USPAT;	1.2002 (00 (22)
	1	((implanting implanted implant) with		2003/02/13
		(silicon (silicon and the si	US-PGPUB	16:34
•		(silicon (silicon adj tetrafluoride)		
		silane dichlorosilane trichlorosilande		
		(Silicon adi tetrachloride) "sik sub 4"		
		"siH.sub4" "siH.sub.2 cl.sub.2"		
Auto-	· .	" SIH. SUD. 2 C1. SUD. 2"		1
•		"siCl.sub.3" "sicl.sub.4"))) and (uniform		
		near3 thickness\$ near3 dielectric)) not		
4		(((438/\$.ccls. or 257/\$.ccls.) and		
		((implanting implant)	4.	. *
	1	((implanting implanted implant) with		
		(nitrogen trifluoronitride ammonia		
		(nitrous adj oxide) (nitric adj oxide)		1
		"n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2	1	
	1	"n.sub.2" "n.sub.2"		
		o" "no"))) and (uniform near3 thickness\$		
	1	near3 dielectric))	₩	
-		("6465373").PN.	HCDAM	1 2002 (2= :=
	1.		USPAT;	2003/02/13
-		//!! ( ) ( 5 2 7 2 11 ) - 22	US-PGPUB	16:35
			USPAT;	2003/02/13
		implanted implant)	US-PGPUB	
	3	(438/\$.ccls. or 257/\$.ccls.) and		16:59
.0	,	//implanting implant	USPAT;	2003/02/13
		((implanting implanted implant) with	US-PGPUB	17:46
1		(nitriding nitridization))		=
	. 4	RTN with (implanting implanted implant	TICDAM	10000 400
,		implantation)	USPAT;	2003/02/13
	255833	capacitor DRAM	US-PGPUB	17:47
	20000	Capacitor DKAM	USPAT;	2003/02/14
			US-PGPUB	
		(capacitor DRAM) and (((implanting		10:54
	122		USPAT;	2003/02/14
	122			
	122	implant implanted) with (angle)) same	US-PGPUB	11:03
	122	implant implanted) with (angle)) same (nitrogen trifluoronitride ammonia	US-PGPUB	11:03
	122	implant implanted) with (angle)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide)	US-PGPUB	11:03
	122	implant implanted) with (angle)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide)	US-PGPUB	11:03
	122	implant implanted) with (angle)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nb.sub.3" "n cub.2	US-PGPUB	11:03
		implant implanted) with (angle)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2- o" "no"))	US-PGPUB	11:03
	122	implant implanted) with (angle)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2- o" "no"))		
		implant implanted) with (angle)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2- o" "no")) (capacitor DRAM) and (((implanting	USPAT;	2003/02/14
		implant implanted) with (angle)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2- o" "no")) (capacitor DRAM) and (((implanting implant implanted)))		2003/02/14
		implant implanted) with (angle)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2- o" "no")) (capacitor DRAM) and (((implanting implant implanted) with (angle angled)) same (nitrogen trifluoronitride ammonia	USPAT;	
		implant implanted) with (angle)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2- o" "no")) (capacitor DRAM) and (((implanting implant implanted) with (angle angled)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide)	USPAT;	2003/02/14
		implant implanted) with (angle)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2- o" "no")) (capacitor DRAM) and (((implanting implant implanted) with (angle angled)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide)	USPAT;	2003/02/14
		implant implanted) with (angle)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2- o" "no")) (capacitor DRAM) and (((implanting implant implanted) with (angle angled)) same (nitrogen trifluoronitride ammonia	USPAT;	2003/02/14

					٠.	
		1	10		USPAT;	2003/02/14
		- 1		implant implanted) with (angle angled))	US-PGPUB	15:07
	-		•	same (nitrogen trifluoronitride ammonia	OD FGFOD	
				(nitrous adj oxide) (nitric adj oxide)	1	7.1
		1		"n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2		
•	,			o" "no"))) not ((capacitor DRAM) and	•	
		-	•	((Capacitor DRAM) and		(1)
		1		(((implanting implant implanted) with	•	
	11 0			(angle)) same (nitrogen trifluoronitride	*	
				ammonia (nitrous adj oxide) (nitric adj		,
				oxide) "n.sub.2" "nf.sub.3" "nh.sub.3"		
				"n.sub.2 o" "no")))	1:	-
	-		34	(capacitor DRAM) and (((doping doped	TICDAM.	1000010011
	}			dope) with (angle angled)) same (nitrogen	USPAT;	2003/02/14
				trifluoronitrido ampare (nitrogen	US-PGPUB	14:04
		ľ		trifluoronitride ammonia (nitrous adj	*	*
				oxide) (nitric adj oxide) "n.sub.2"	į.	
			0.40	"nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))		
٠.		1	242		USPAT;	2004/05/17
				implant implanted) with (angle angled))	US-PGPUB	14:27
			,	same (silicon (silicon adj tetrafluoride)	OD LOLOD	14:27
				silane dichlorosilane trichlorosilande		
	•			(silicon adj tetrachloride) "siF.sub.4"		
				"siH.sub4" "siH.sub.2 cl.sub.2"		
				"aiCl sub 2" "		
			1 -	"siCl.sub.3" "sicl.sub.4"))		
			15		USPAT;	2003/02/14
				dope   with (angle angled)   same (nitrogen	US-PGPUB	14:06
		1		trilluoronitride ammonia (nitrous adi	05 1010B	14.00
				oxide) (nitric adj oxide) "n.sub.2"		
- 1				"nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")))		
- 1		1 '		not ((capacitor DRAM) and (((implanting	-	
			4.	implant implanted with (((Implanting	,	
				implant implanted) with (angle angled))		
- 1		9		same (nitrogen trifluoronitride ammonia	1,	
				(nitrous adj oxide) (nitric adj oxide)		
				"n. sub. 2" "nf. sub. 3" "nh sub 3" "n sub 2.		
			*	[O" "no")))		
	-		170	((capacitor DRAM) and (((implanting	USPAT;	2002/02/14
-				implant implanted) with (angle angled))		2003/02/14
- 1		1		same (silicon (silicon adj tetrafluoride)	US-PGPUB	14:46
				silane dichlorosilane trichlorosilande		
1.		1		/giligon add total light trichlorosilande		
	•			(silicon adj tetrachloride) "siF.sub.4"	* . * *	
				"siH.sub4" "siH.sub.2 cl.sub.2"		K
١.			i	"siCl.sub.3" "sicl.sub.4"))) not		
	χ.*		•	((Capacitor DRAM) and (((implanting		
	•			implant implanted) with (angle angled))		
				same (nitrogen trifluoronitride ammonia		
				(nitrous adj oxide) (nitric adj oxide)		
		1 2		"n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2		
		1		o" "no")))		
-	<del>-</del> , .	1.	180			
		1	1200	(capacitor DRAM) and (((implanting	USPAT;	2003/02/14
		1 .	- 1	implant implanted) same (angle angled))	US-PGPUB	15:22
1				same (nitrogen trifluoronitride ammonia	•	
		1		(nitrous adj oxide) (nitric adj oxide)		
	5 +	1.		"n.sub.2" "nf.sub.3" "nh.sub.3" "n sub.2		
	* (1)	1		o" "no"))		
'		1	27	(uniform uniformity) with ((silicon adj	IICD N m	10000 (00 )
				nitride) "si.sub.3 N.sub.4") with	USPAT;	2003/02/14
1				(implanting implanted down a design of the control	US-PGPUB	14:49
	•			(implanting implanted doped doping doped implant)		
-	- 4	1	58		+ :1	
			26	((capacitor DRAM) and (((implanting	USPAT;	2003/02/14
			.	implant implanted) same (angle angled))	US-PGPUB	15:04
				same (nitrogen trifluoronitride ammonia		10.04
				(nitrous adi oxide) (nitric adi ovido)	·	
			- 1	"n.sub.2" "nf.sub.3" "nh.sub.3" "n sub.2		
		-	.	o" "no"))) not ((capacitor DRAM) and		
				(((implanting implant implanted) with		
1			•	(angle)) same (nitratic implanted) With	ł	`
	000			(angle)) same (nitrogen trifluoronitride	,	
1			- 1	ammonia (nitrous adj oxide) (nitric adj		*
			- 1	OXIGE) "n.sub.2" "nf.sub.3" "nh.sub.3"	j	
<u>_</u>	· .		L	"n.sub.2 o" "no")))	ì	,

1		- 4					1000	
,	_		1.7	135	(capacitor DRAM) and (((doping doped	USPAT;	2003/02/14	
					dope   same (angle angled)   same (nitrogen	US-PGPUB	15:17	*
					trifluoronitride ammonia (nitrous adi		13.1	
	-				oxide) (nitric adj oxide) "n.sub.2"	, a		.
	]	- 1		304	"nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))			
	0			304	i transmission bidail and titlingian in	USPAT;	2003/02/14	
÷				24	implant implanted) same (angle angled))	US-PGPUB	15:20	
	4 -			• 7	same (silicon (silicon adj tetrafluoride)			
		,	e +		silane dichlorosilane trichlorosilande			-
	٠.	1			(silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2"			<i>.</i>
					"siCl.sub.3" "sicl.sub.4"))			
	<b>-</b>			41	((capacitor DRAM) and (((implanting			
		- }			implant implanted) same (angle angled))	USPAT;	2003/02/14	.
		1	•		same (silicon (silicon adj tetrafluoride)	US-PGPUB	15:14	
4	•		,		sliane dichlorosilane trichlorosilande			
-			,		(Silicon adj tetrachloride) "siF sub 4"	·		:
٠.,				a	"SiH.sub4" "siH.sub.2 cl sub 2"	0		.
-	• *				"siCl.sub.3" "sicl.sub.4"))) not			.
-					(((capacitor DRAM) and (((implanting	•		1
	* . *			.	implant implanted) with (angle angled))			
					same (silicon (silicon adj tetrafluoride)			
-	10				silane dichlorosilane trichlorosilande	1.	1.	$\cdot \mid$
-	10 1	*   -			(silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2"	100		*
		-   -			"siCl.sub.3" "sicl.sub.4"))) ((capacitor			
	£*	ļ.,		14.	DRAM) and (((implanting implant		, ,	1
-					implanted) with (angle)) same (nitrogen			
		1.	_		trifluoronitride ammonia (nitrous adj		*	
					oxide) (nitric adj oxide) "n sub 2"	. *		
					"nr.sub.3" "nh.sub.3" "n.sub.2 o" "no")))		, v	
				*	(((Capacitor, DRAM) and (((implanting			
			1		implant implanted) same (angle angled))			
	*				same (nitrogen trifluoronitride ammonia			
			. •		(nitrous adj oxide) (nitric adj oxide)			ŀ
	1000				"n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2			
				; *	o" "no"))) not ((capacitor DRAM) and (((implanting implant implanted) with	17.	,	
	•				(angle)) same (nitrogen, trifluoronitride			١.
٠.			•		ammonia (nitrous adj oxide) (nitric adj	, * <b>.</b>		
					oxide) "n.sub.2" "nf.sub.3" "nb.sub.2"	₹ <sub>6</sub> *		
	4 .		10		"n.sub.2 o" "no")))))			-
ŀ.	-	1		1	("6326277").PN.	USPAT;	2003/02/14	
2						US-PGPUB	15:14	1
			*	1	(("6326277").PN.) and (silicon adj	USPAT;	2003/02/14	
1.				] ]	nitride).	US-PGPUB	15:15	
			-	311	(capacitor DRAM) and (((doped doping	USPAT;	2003/02/14	
			*	, J.	dope) same (angle angled)) same (silicon	US-PGPUB 1	15:19	1
	: ·	-			(silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon			:
		ŀ	r	1	adj tetrachloride) "siF.sub.4" "siH.sub4"			
1.					siH.sub.2 cl.sub.2" "siCl.sub.3"			-
1				· 1	'sicl.sub.4"))			1
-	-		2	203	((capacitor DRAM) and ((doped doping	USPAT;	0000 (00 (00	
		1		9	lope) same (angle angled)) same (silicon	US-PGPUB	2003/02/14	
				1 '	(SITICON ad) tetrafluoride) silana	OD-FGPUD	15:20	
			· • ·	· c	lichlorosilane trichlorosilande (silicon			.
				j ē	d] tetrachloride) "siF sub 4" "siH sub/"	*		
. *			٠.	4	SIH.SUD.2 Cl.sub.2" "siCl sub 3"			1
			,	1.,	sicl.sub.4"))) not ((capacitor DRAM) and	₹.	*	1.
	, .			.   1	((implanting implant implanted) same			
•	6	ľ			angle angled)) same (silicon (silicon dj tetrafluoride) silane dichlorosilane			. *
				t	richlorosilande (silicon adj	*	· · · · · · · · · · · · · · · · · · ·	
	<i>i.</i>	,		t	etrachloride) "siF sub 4" "siH sub4"	*		ŀ
				"	SIH. Sub. 2 cl. sub. 2" "siCl sub 3"	. 4		
-				"	sicl.sub.4")))			
	•							ĺ

					1 × 1
-		7	4 ((capacitor DRAM) and ((doping doped	USPAT;	2003/02/14
1			dope) same (angle angled)) same (nitroger		
1			trifluorenitural	US-PGPUB	15:21
_	- '	-	trifluoronitride ammonia (nitrous adj		
			oxide) (nitric adj oxide) "n.sub.2"		
- 1			"nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")))		
	• 00		not //ganagitan DDTM		* ***
ł			not ((capacitor DRAM) and (((implanting		, in the second of the second
-			implant implanted) same (angle angled))		
		-	same (nitrogen trifluoronitride ammonia		
- 1			(nitrous add ovide) (nitrous anumonita		
1			(nitrous adj oxide) (nitric adj oxide)		
.	γ ř	1	"n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2		v .
	` ,		o" "no")))		
-		20.	(((capacitor DRAM) and (((doped doping		
i				USPAT;	2003/02/14
		,	dope) same (angle angled)) same (silicon	US-PGPUB*	15:23
			(silicon adj tetrafluoride) silane	05 10105	13.23
		F .	dichlorosilane trichlorosilande (silicon	, , , , ,	,
1			add to the shift of the state o	-	,
- 1		1	adj tetrachloride) "siF.sub.4" "siH.sub4"	H.	
		1	"SlH.sub.2 cl.sub.2" "siCl sub 3"		
		1	"sicl sub 4"\\\ not: //generate press		
			"sicl.sub.4"))) not ((capacitor DRAM) and		
		l	((Implanting implant implanted) same		1. 7. 6
			(angle angled)) same (silicon (silicon		
1 .	*	1	adj tetrafluoride) silane dichlorosilane	1	The state of
		1	trichlanarilaria sitane dichiorosilane	1	*
		1 -	trichlorosilande (silicon adj	1 .	
1 .			tetrachloride) "siF.sub.4" "siH sub4"	* ,	* 0.00
1.			"siH.sub.2 cl.sub.2" "siCl.sub.3"	*	1
1 .			"eigl gub 4")	1	1
			"sicl.sub.4"))) ) not ((capacitor_DRAM)		
			. and (((implanting implant implanted) with		
i			(angle angled)) same (silicon (silicon		1
		·	add totas floored by		
1			adj tetrafluoride) silane dichlorosilane		
			trichlorosilande (silicon adi	1	1
1			tetrachloride) "siF.sub.4" "siH.sub4"		
	•	: '	"sill sub 2 sl sub OH H is		
			"siH. sub.2 cl. sub.2" "siCl. sub.3"		
		•	"sicl.sub.4")))		
1.	i	198	(((capacitor DRAM) and (((doped doping	HODAM	
1			dope) same (angle angled)) same (silicon	USPAT;	2003/02/14
			(silicon	US-PGPUB	15:24
1 .	. 1		(silicon adj tetrafluoride) silane		
			dichlorosilane trichlorosilande (silicon		
1	.	2.4	adj tetrachloride) "siF.sub.4" "siH.sub4"		
,	· 1		"gill gul 2 -1 -1 - Sub.4" "SIH. Sub4""	· .	
			"siH.sub.2 cl.sub.2" "siCl.sub.3"		• ' '
1	5 1		"SICI.sub.4"))) not ((capacitor DDAM) and		
		,	(((implanting implant implanted) same		
			(angle angled)) arms (in the same		* * * * * * * * * * * * * * * * * * * *
	1		(angle angled)) same (silicon (silicon		
	1		adj tetrafluoride) silane dichlorosilane		196 x 2
1 -	_, _ l		trichlorosilande (silicon adi		· · · · · · · · · · · · · · · · · · ·
1	· .		tetrachloride) "siF.sub.4" "siH.sub4"		
1			"sill sub 2 =1 ==1 0" "SIH. sub4"	<u> </u>	
	1 1		"siH.sub.2 cl.sub.2" "siCl.sub.3"		*
1		* .	["sicl.sub.4"))) ) not ((capacitor DDAM)		
	1		and (((implanting implant implanted) same	, '	•
1.	ŀ		(angle angled)) same		• .
			(allyte didited)) same (nitrogen	, '	
1	.		trifluoronitride ammonia (nitrous adi		
* **	·#"		OXIGE) (nitric adi oxide) "n sub 2"	; ,	the state of the s
1			"nf sub 3" "nb sub 2" "		
l _			"nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")))		
		1	09/385787	USPAT;	2002/02/14
· '					2003/02/14
-	. 1	1	("6159785").PN.	US-PGPUB	15:32
			1	USPAT;	2003/02/14
h	.			US-PGPUB	15:32
-		. 1	(("6159785").PN.) and (silicon adj		
		·	nitride)	USPAT;	2003/02/14
-		3		US-PGPUB	15:32
		3	(capacitor DRAM) and (((implanting	USPAT;	2003/02/14
			implant implanted done doning doned) with	•	
			(angle angled)) same (nitrogen "si.sub.3	US-PGPUB	15:47
		* .	n sub 4"\\ ==== (nitrogen "si.sub.3		
_	1		n. Sup. 4") same (uniformity uniform)		. 1
<del>-</del> .	.	1	("6204142").PN.	HCDAM.	2004/05/4
	.			USPAT;	2004/05/17
- * .		7641	(Shin).in.	US-PGPUB	16:46
		, 041	Apirtill · TH ·		2004/05/17
		,			10.46
<del>-</del>	1.00	1	"20010018787"		16:46
		•	• • • • • • • • • • • • • • • • • • • •	USPAT;	2004/05/17
					16:46
1.5					

1 - '				
] =	11 (("4963506") or ("5663087") or	USPAT;	2004/05/17	ī
· .	("5882978") or ("5939333") or ("5981404")	US-PGPUB	17:59	
	or ("6077754") or ("6147013") or	OD FOLOR	17:59	
	("6171977") or ("6258690") or ("6268299")			ĺ
	or ("6284583")).PN.		• * *	1.
	, ( 323 1865 // . IN.		1	